Jongwon Lee

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | A Novel High-Speed Multiplexing IC Based on Resonant Tunneling Diodes. IEEE Nanotechnology Magazine, 2009, 8, 482-486. | 2.0 | 25 |
| 2 | An On–Off Mode RTD Oscillator Operating at Extremely Low Power Consumption. IEEE Nanotechnology Magazine, 2012, 11, 863-865. | 2.0 | 17 |
| 3 | Reflection-Type RTD Low-Power Amplifier With Deep Sub-mW DC Power Consumption. IEEE Microwave and Wireless Components Letters, 2014, 24, 551-553. | 3.2 | 15 |
| 4 | A 675 GHz Differential Oscillator Based on a Resonant Tunneling Diode. IEEE Transactions on Terahertz Science and Technology, 2016, 6, 510-512. | 3.1 | 14 |
| 5 | A Low-Power 40-Gb/s 1:2 Demultiplexer IC Based on a Resonant Tunneling Diode. IEEE Nanotechnology Magazine, 2012, 11, 431-434. | 2.0 | 9 |
| 6 | RF Power Analysis on 5.8 GHz Low-Power Amplifier Using Resonant Tunneling Diodes. IEEE Microwave and Wireless Components Letters, 2017, 27, 61-63. | 3.2 | 9 |
| 7 | 40 Gb/s Low-Power 4:1 Multiplexer Based on Resonant Tunneling Diodes. IEEE Nanotechnology Magazine, 2012, 11, 890-895. | 2.0 | 8 |
| 8 | 692 GHz High-Efficiency Compact-Size InP-Based Fundamental RTD Oscillator. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 716-719. | 3.1 | 7 |
| 9 | A Low DC-Power Multiplexer IC using an InP-based CML-MOBILE RTD/HBT Technology. , 2008, , . | | 4 |
| 10 | 5 GHz low-power RTD-based amplifier MMIC with a high figure-of-merit of 24.5 dB/mW. , 2013, , . | | 4 |
| 11 | Implementation of a 4∶1 multiplexing quantum-effect IC based on RTD circuit topology. , 2010, , . | | 3 |
| 12 | Area-Efficient Series-Connected Resonant Tunneling Diode Pair as Binary Neuron in Cellular Neural Network. IEEE Electron Device Letters, 2020, 41, 1308-1311. | 3.9 | 2 |
| 13 | 225â€GHz tripleâ€push RTD oscillator with 0.5â€mW dcâ€power consumption. IET Circuits, Devices and Systems, 2020, 14, 209-215. | 1.4 | 1 |
| 14 | Sidewall Slope Control of InP Via Holes for 3D Integration. Micromachines, 2021, 12, 89. | 2.9 | 1 |
| 15 | Implementation of Flip-Chip Microbump Bonding between InP and SiC Substrates for Millimeter-Wave Applications. Micromachines, 2022, 13, 1072. | 2.9 | 1 |
| 16 | Implementation of a New Functional Digital IC for Multiplexing Operation Based on RTDs. , 2008, , . | | 0 |
| 17 | A 1.3 pJ/bit energy-efficient ultra-low power on-off mode oscillator using an InP-based quantum-effect tunneling device. , 2012, , . | | 0 |
| 18 | A sub-mW D-band 2 nd harmonic oscillator using InP-based quantum-effect tunneling devices. , 2014, , . | | 0 |

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|----|---|-----|-----------|
| 19 | Negative-differential-conductance RTD amplifier MMIC with record foms of gain-to-dc power ratio and noise figure. , 2014, , . | | 0 |
| 20 | Characterization of a selfâ€aligned RTD using a SiNx sidewall process for highâ€speed applications. Microwave and Optical Technology Letters, 2017, 59, 3073-3076. | 1.4 | 0 |
| 21 | Noise analysis of reflectionâ€ŧype microwave RTD amplifier. IET Circuits, Devices and Systems, 2020, 14, 966-971. | 1.4 | 0 |